

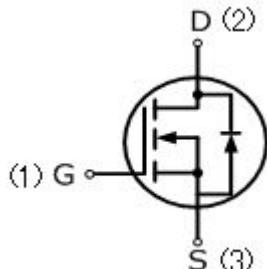


MIC-IRF630

9 Amps, 200 Volts N-CHANNEL MOSFET

Features

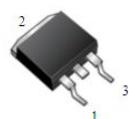
- 9A, 200V, $R_{DS(ON)MAX} = 0.3 \Omega$ @ $V_{GS}=10V/4.5A$
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220AB



ITO-220AB



TO-263



TO-262

Absolute Maximum Ratings($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	MIC-IRF630	UNIT
Drain-Source Voltage	V_{DSS}	200	V
Gate-Source Voltage	V_{GSS}	± 30	
Continuous Drain Current	I_D	9	A
Pulsed Drain Current(Note 1)	I_{DM}	36	
Single Pulse Avalanche Energy(Note 2)	E_{AS}	460	mJ
Avalanche Current(Note 1)	I_{AR}	9	A
Repetitive Avalanche Energy(Note 1)	E_{AR}	23	mJ
Maximum Power Dissipation	P_D	83	W
Reverse Diode dV/dt (Note 3)	dv/dt	5.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	260	°C
Mounting Torque	6-32 or M3 screw	10	lbf • in
		1.1	N • m

Thermal Characteristics

Parameter	Symbol	MIC-IRF630	Units
Maximum Junction-to-Case	R_{thJC}	1.5	°C/W



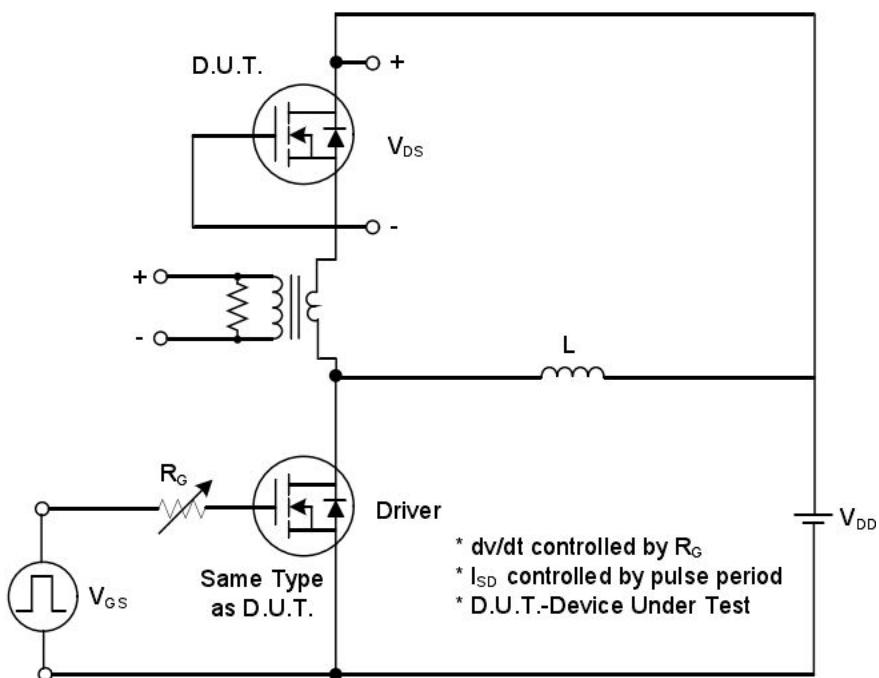
Electrical Characteristics ($T_c=25^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	200	—	—	V
Breakdown Temperature Coefficient $/\Delta T_J$	$\Delta \text{BV}_{\text{DSS}}$	Reference to 25°C , $\text{I}_D=250\mu\text{A}$	—	0.6	—	$\text{V}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=200\text{V}, \text{V}_{\text{GS}}=0\text{V}$	—	—	25	μA
Gate-Body Leakage Current, Forward	I_{GSSF}	$\text{V}_{\text{GS}}=30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	0.1	μA
Gate-Body Leakage Current, Reverse	I_{GSSR}	$\text{V}_{\text{GS}}=-30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	-0.1	μA
On Characteristics						
Gate-Source Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=10\text{V}, \text{I}_D=250\mu\text{A}$	2	—	4	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=4.5\text{A}$	—	—	0.3	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=25\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $f=1.0\text{MHz}$	—	—	860	pF
Output Capacitance	C_{oss}		—	—	160	pF
Reverse Transfer Capacitance	C_{rss}		—	—	100	pF
Switching Characteristics						
Turn-On Delay Time	$t_{\text{d(on)}}$	$\text{V}_{\text{DD}}=100\text{V}, \text{I}_D=9\text{A},$ $\text{R}_g=25\Omega$ (Note 4,5)	—	30	—	ns
Turn-On Rise Time	t_r		—	65	—	ns
Turn-Off Delay Time	$t_{\text{d(off)}}$		—	26	—	ns
Turn-Off Fall Time	t_f		—	8	—	ns
Total Gate Charge	Q_g	$\text{V}_{\text{DS}}=160\text{V}, \text{I}_D=9\text{A},$ $\text{V}_{\text{GS}}=10\text{V}$, (Note 4,5)	—	17	—	nC
Gate-Source Charge	Q_{gs}		—	10	—	nC
Gate-Drain Charge	Q_{gd}		—	7	—	nC
Drain-Source Body Diode Characteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S		—	—	9	A
Pulsed Diode Forward Current	I_{SM}		—	—	36	A
Diode Forward Voltage	V_{SD}	$\text{I}_S=9\text{A}, \text{V}_{\text{GS}}=0\text{V}$	—	—	1.0	V
Reverse Recovery Time	t_{rr}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=8\text{A},$ $d\text{I}_f/dt=100\text{A/us}$, (Note 4)	—	380	—	ns
Reverse Recovery Charge	Q_{rr}		—	7.0	—	μC

Notes

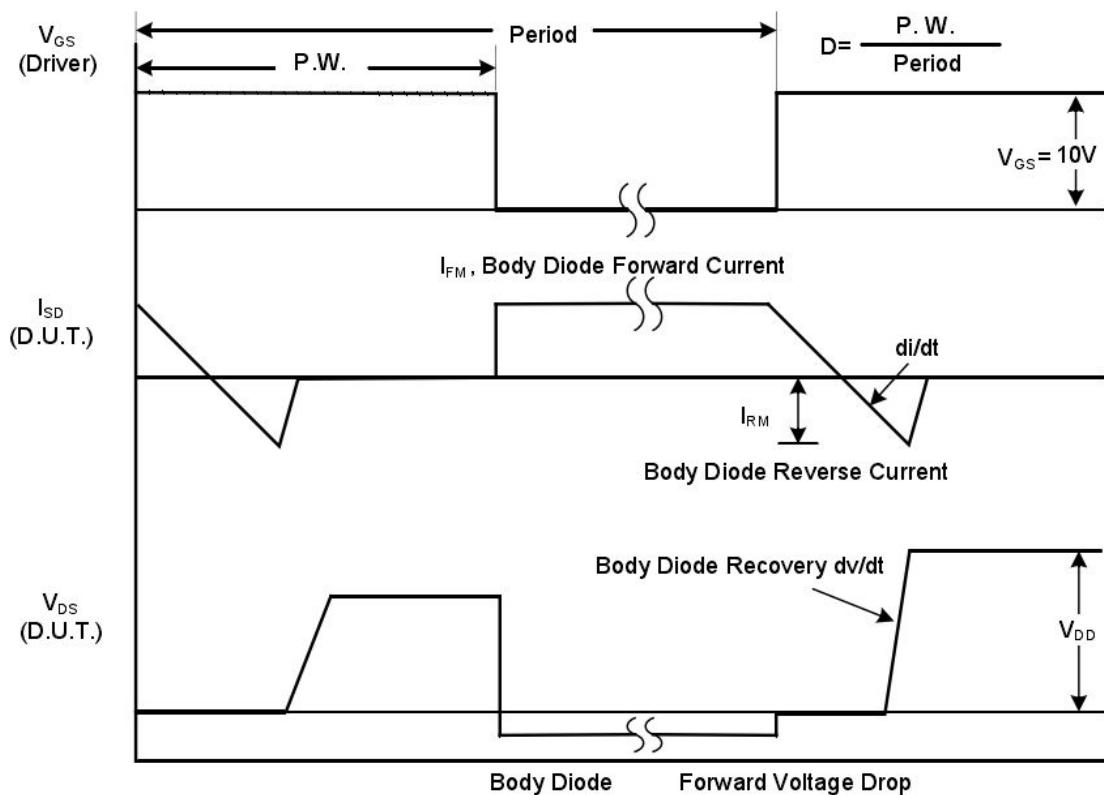
- Repetitive Rating: pulse width limited by maximum junction temperature.
- $\text{V}_{\text{DD}}=50\text{V}, L=8.5\text{mH}, R_g=25\Omega, I_{\text{AS}}=9\text{A}$, starting $T_J=25^\circ\text{C}$.
- $I_{\text{SD}} \leq I_D, dI/dt=200\text{A/us}, V_{\text{DD}} \leq \text{BV}_{\text{DSS}}$, starting $T_J=25^\circ\text{C}$.
- Pulse width $\leq 300\text{us}$; duty cycle $\leq 2\%$.
- Repetitive rating; pulse width limited by maximum junction temperature.



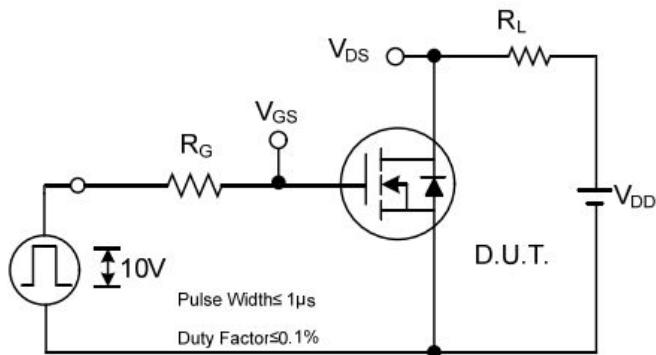
TEST CIRCUIT AND WAVEFORM



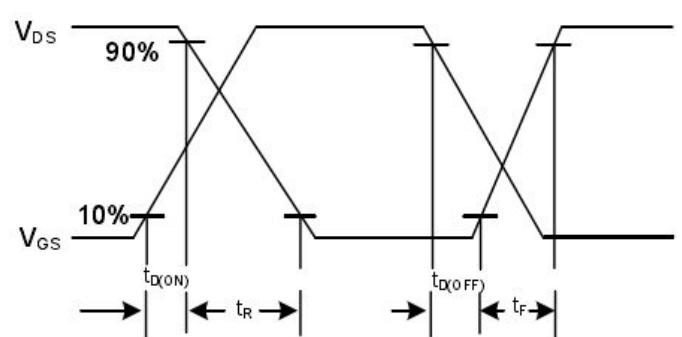
Peak Diode Recovery dv/dt Test Circuit



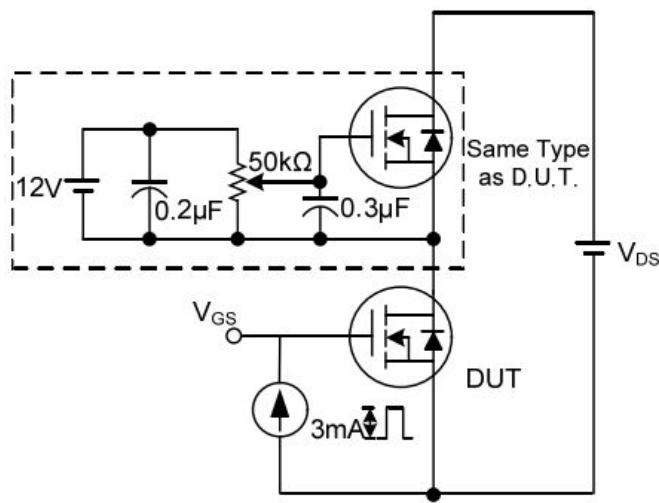
Peak Diode Recovery dv/dt Waveforms



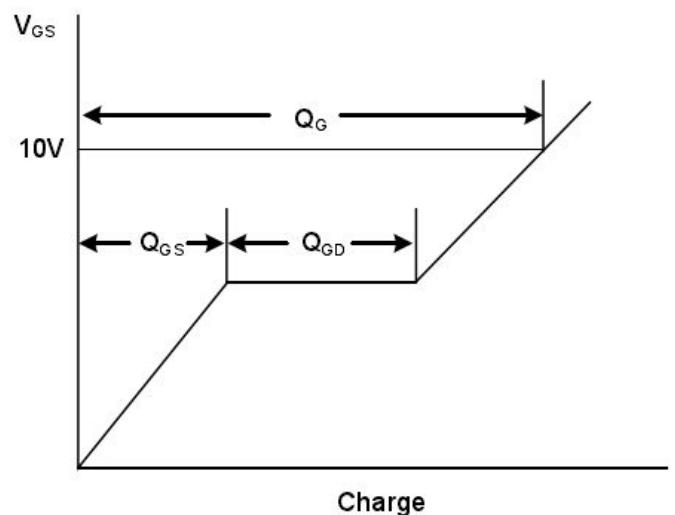
Switching Test Circuit



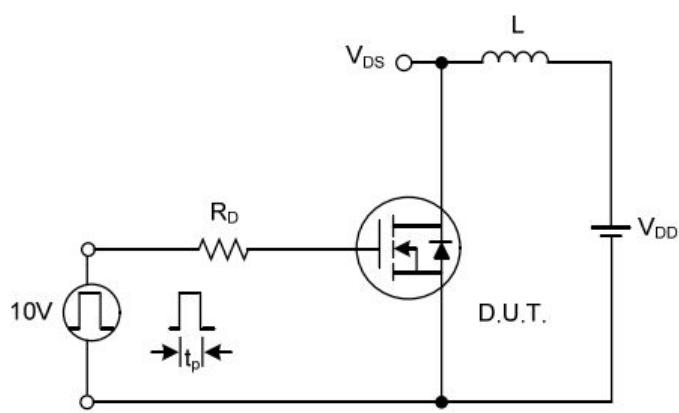
Switching Waveforms



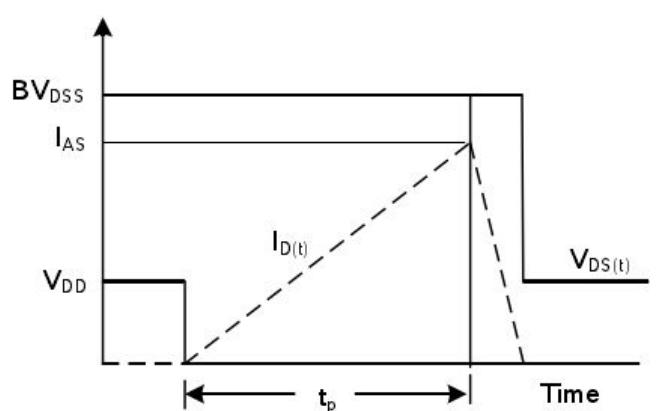
Gate Charge Test Circuit



Gate Charge Waveform



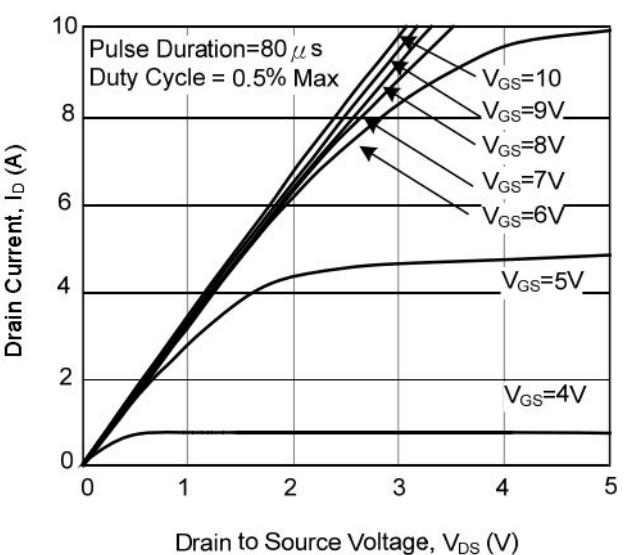
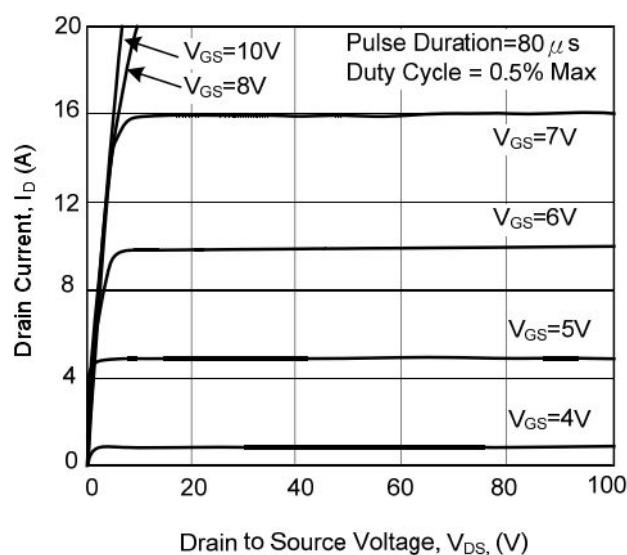
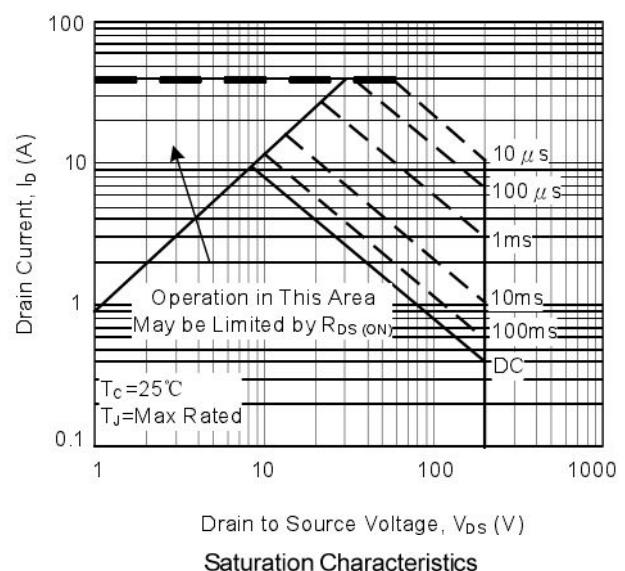
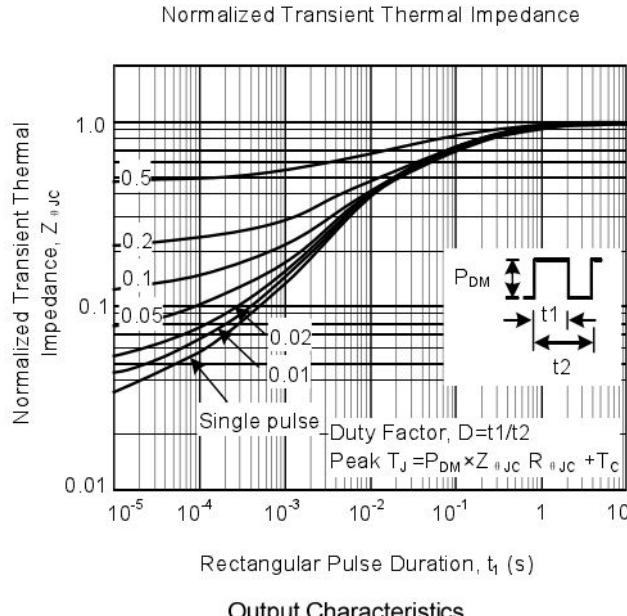
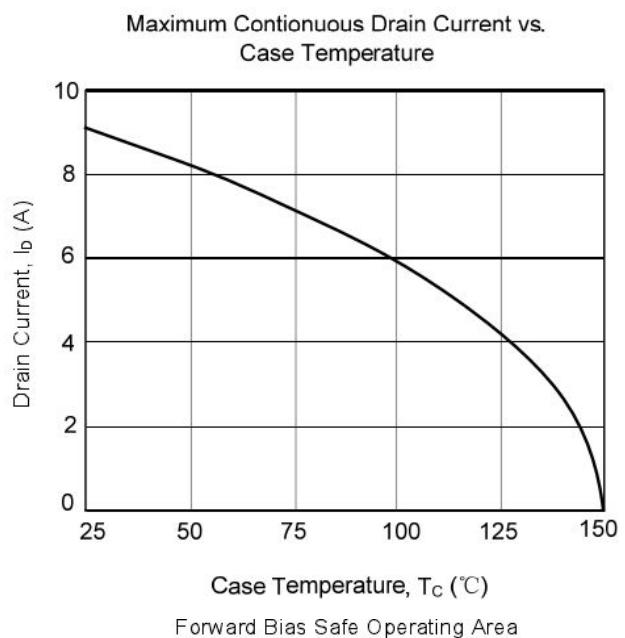
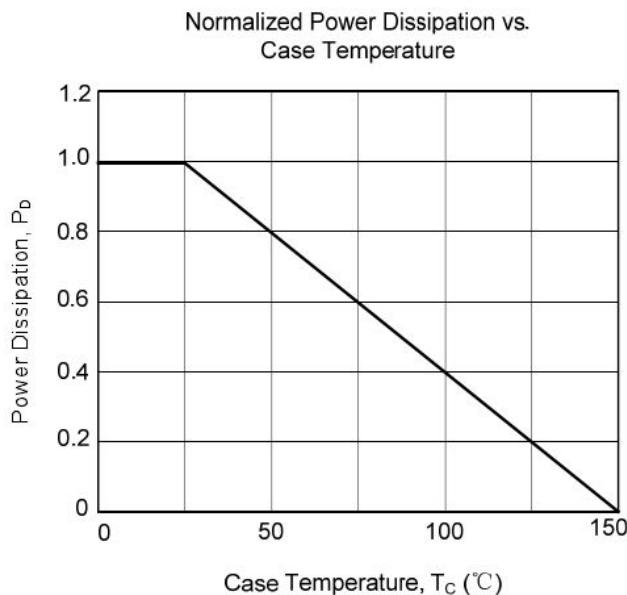
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

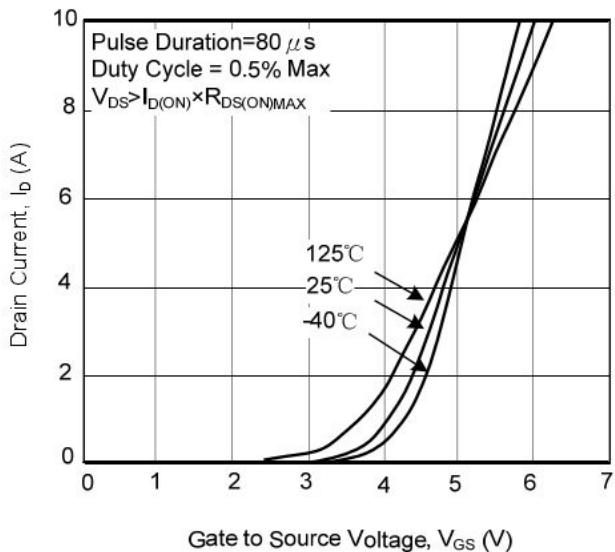


RATING AND CHARACTERISTIC CURVES

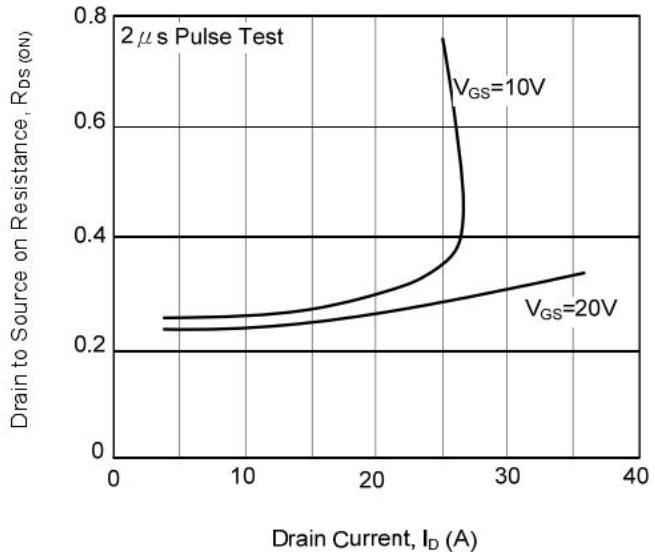




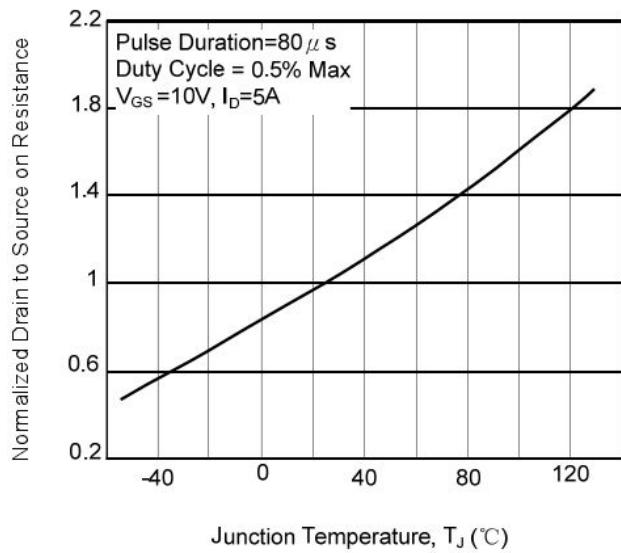
Transfer Characteristics



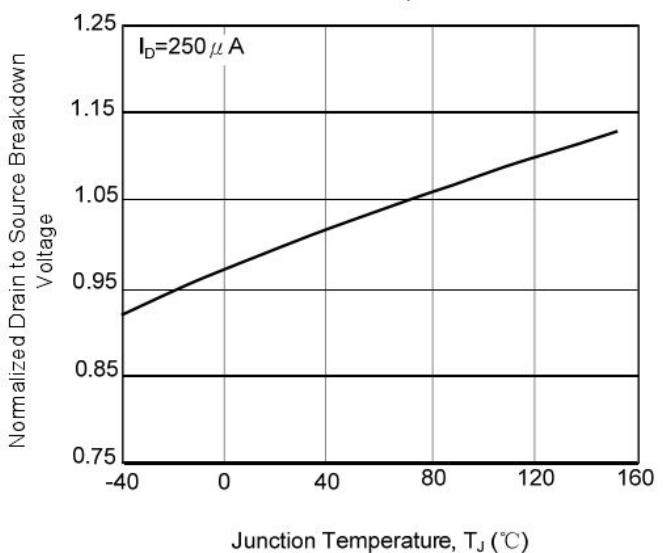
Drain to Source on Resistance vs.
Gate Voltage and Drain Current



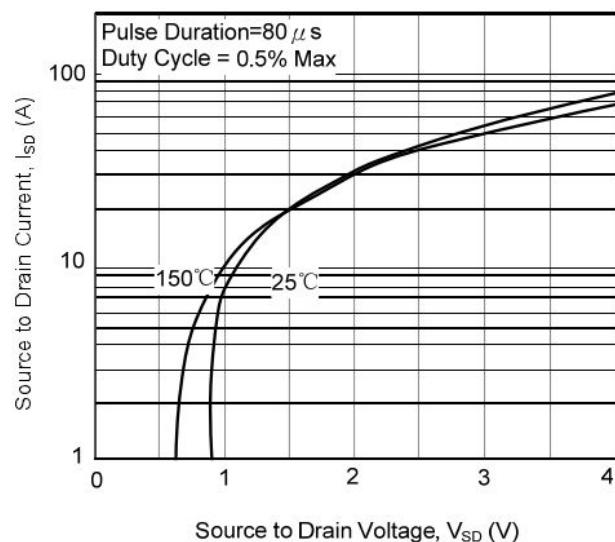
Normalized Drain to Source on Resistance vs.
Junction Temperature



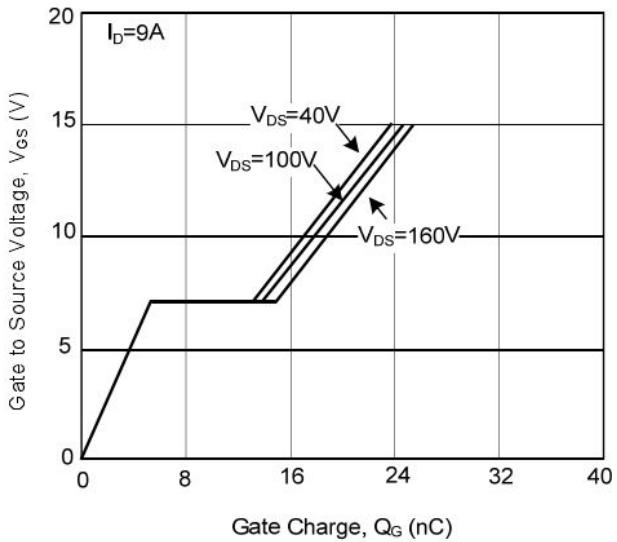
Normalized Drain to Source Breakdown Voltage vs.
Junction Temperature



Source to Drain Diode Voltage



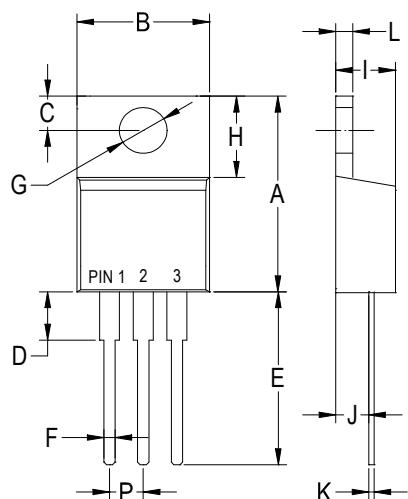
Gate to Source Voltage vs. Gate Charge





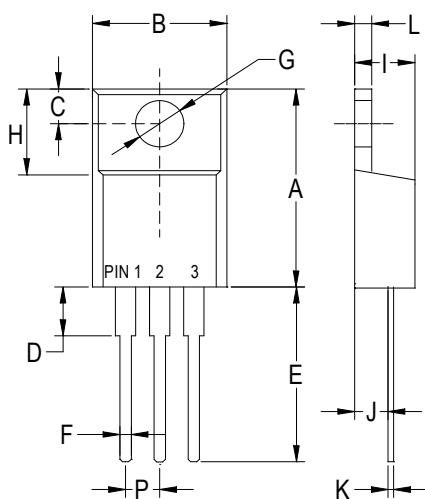
PACKAGE OUTLINE DIMENSIONS

TO-220AB



TO-220AB		
Dim	Min	Max
A	.573 (14.55)	.603 (15.32)
B	—	.412 (10.5)
C	.103 (2.62)	.113 (2.87)
D	.140 (3.56)	.160 (4.06)
E	.510 (13.0)	.560 (14.3)
F	.027 (0.68)	.037 (0.94)
G	.148 (3.74)	.154 (3.91)
H	.230 (5.84)	.270 (6.86)
I	.175 (4.44)	.185 (4.86)
J	.100 (2.54)	.110 (2.79)
K	.014 (0.35)	.025 (0.64)
L	.045 (1.14)	.055 (1.40)
P	.095 (2.41)	.105 (2.67)

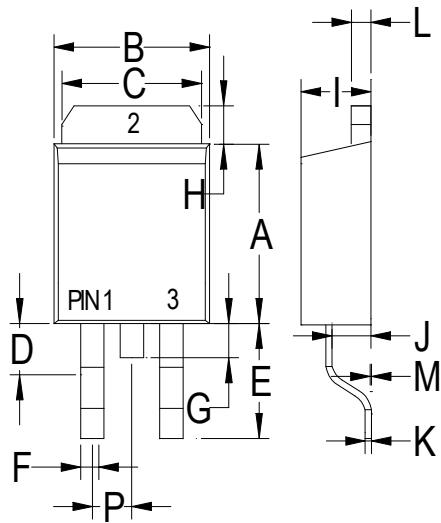
ITO-220AB



ITO-220AB		
Dim	Min	Max
A	.571 (14.5)	.610 (15.5)
B	.383 (9.72)	.406 (10.3)
C	.110 (2.80)	.126 (3.20)
D	.133 (3.38)	.162 (4.10)
E	.512 (13.0)	.551 (14.0)
F	.028 (0.70)	.035 (0.90)
G	.114 (2.90)	.138 (3.50)
H	.268 (6.80)	.291 (7.40)
I	.162 (4.10)	.185 (4.70)
J	.102 (2.60)	.110 (2.80)
K	.018 (0.45)	.026 (0.65)
L	.097 (2.46)	.113 (2.86)
P	.890 (2.25)	.113 (2.85)



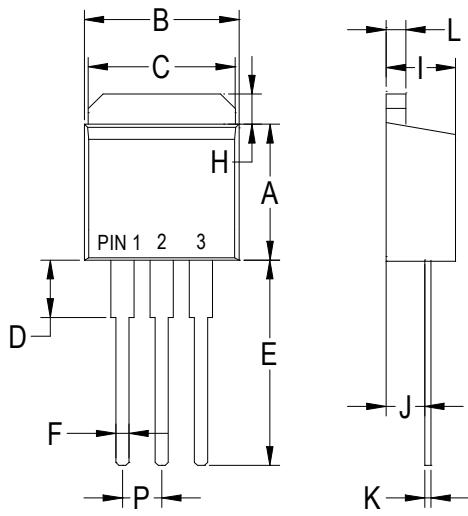
TO-263



TO-263		
Dim	Min	Max
A	.323 (8.20)	.348 (8.85)
B	.394 (10.0)	.413 (10.5)
C	.394 (10.0)	.402 (10.2)
D	.077 (1.95)	.100 (2.55)
E	.204 (5.17)	.227 (5.77)
F	.027 (0.68)	.037 (0.94)
G	--	.067 (1.70)
H	.046 (1.17)	.053 (1.34)
I	.175 (4.44)	.191 (4.86)
J	.100 (2.54)	.110 (2.79)
K	.014 (0.35)	.025 (0.64)
L	.047 (1.20)	.055 (1.40)
M	.000 (0.00)	.010 (0.25)
P	.095 (2.41)	.105 (2.67)

Dimensions in inches and (millimeters)

TO-262



TO-262		
Dim	Min	Max
A	.323 (8.20)	.348 (8.85)
B	.394 (10.0)	.413 (10.5)
C	.394 (10.0)	.402 (10.2)
D	.140 (3.56)	.160 (4.06)
E	.510 (13.0)	.560 (14.3)
F	.027 (0.68)	.037 (0.94)
G	.046 (1.17)	.053 (1.34)
I	.175 (4.44)	.185 (4.86)
J	.100 (2.54)	.110 (2.79)
K	.014 (0.35)	.025 (0.64)
L	.045 (1.14)	.055 (1.40)
P	.095 (2.41)	.105 (2.67)